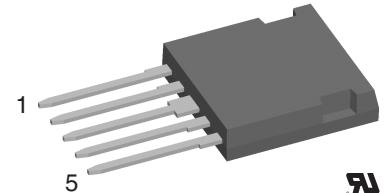
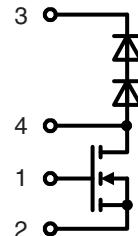


HiPerFET™
CoolMOS™¹⁾ Power MOSFETs
-Boost Chopper Topology-
in ISOPLUS i4-PAC™

I_{D25} = 38 A
V_{DSS} = 600 V
R_{DSon} = 60 mΩ



MOSFET

Symbol	Conditions	Maximum Ratings		
V _{DSS}	T _{VJ} = 25°C to 150°C	600	600	V
V _{GS}		±20	±20	V
I _{D25}	T _C = 25°C	38	38	A
I _{D90}	T _C = 90°C	25	25	A

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)	min.	typ.
R _{DSon}	V _{GS} = 10 V; I _D = 20 A		60	70
V _{Gsth}	V _{DS} = 20 V; I _D = 2.7 mA	2.1		3.9
I _{DSS}	V _{DS} = V _{DSS} ; V _{GS} = 0 V; T _{VJ} = 25°C T _{VJ} = 125°C		250	25 μA
I _{GSS}	V _{GS} = ±20 V; V _{DS} = 0 V			200 nA
Q _g Q _{gs} Q _{gd}	V _{GS} = 10 V; V _{DS} = 350 V; I _D = 47 A		250 25 120	nC nC nC
t _{d(on)} t _r t _{d(off)} t _f	V _{GS} = 10 V; V _{DS} = 380 V; I _D = 47 A; R _G = 1.8 Ω		20 30 110 10	ns ns ns ns
V _F	(reverse conduction) I _F = 20 A; V _{GS} = 0 V	0.9		V
R _{thJC} R _{thJS}		tbd	0.45 K/W 0.45 K/W	

Features

- fast CoolMOS™¹⁾ power MOSFET
3rd generation
 - high blocking voltage
 - low on resistance
 - low thermal resistance due to reduced chip thickness
- HiPerDyn™ FRED
 - consisting of series connected diodes
 - enhanced dynamic behaviour for high frequency operation
- ISOPLUS i4-PAC™ package
 - isolated back surface
 - low coupling capacity between pins and heatsink
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - industry standard outline
 - UL registered, E 72873

Applications

- chopper for power factor correction
- supply of high frequency transformer
 - switched mode power supplies
 - welding converters

¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

Free Wheeling Diode (data for series connection)

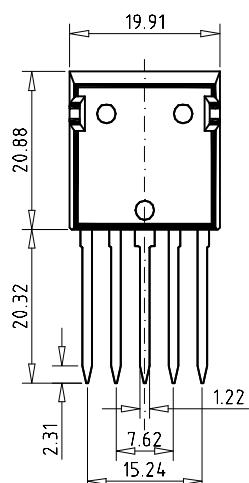
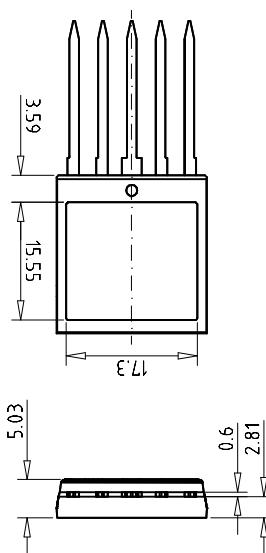
Symbol	Conditions	Maximum Ratings		
V_{RRM}	$T_{VJ} = 25^\circ\text{C}$ to 150°C	600		V
I_{F25}	$T_c = 25^\circ\text{C}$	80		A
I_{F90}	$T_c = 90^\circ\text{C}$	45		A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 20 \text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.6 2.0	2.9 V	V
I_R	$V_R = V_{RRM}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.25	0.25 mA mA	
I_{RM} t_{rr}	$\left. \begin{array}{l} I_F = 30 \text{ A}; dI_F/dt = -500 \text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C} \\ V_R = 300 \text{ V} \end{array} \right\}$	9 40		A ns
R_{thJC} R_{thJS}	(per diode)	tbd	0.65 K/W K/W	

Component

Symbol	Conditions	Maximum Ratings		
T_{VJ}		-55...+150		°C
T_{stg}		-55...+125		°C
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500		V~
F_c	mounting force with clip	20...120		N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
C_p	coupling capacity between shorted pins and mounting tab in the case	40		pF
d_s, d_A	pin - pin	1.7		mm
d_s, d_A	pin - backside metal	5.5		mm
Weight		9		g

Dimensions in mm (1 mm = 0.0394")

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